Amplifier Transistors

PNP Silicon

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage BC556 BC557 BC558	V _{CEO}	-65 -45 -30	Vdc
Collector - Base Voltage BC556 BC557 BC558	V _{СВО}	-80 -50 -30	Vdc
Emitter - Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current – Continuous – Peak	I _C	-100 -200	mAdc
Base Current – Peak	I _{BM}	-200	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0	mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

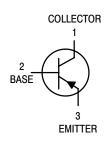
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction–to–Case	$R_{ heta JC}$	83.3	°C/W

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



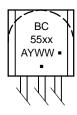
ON Semiconductor®

http://onsemi.com





MARKING DIAGRAM



BC55x = Device Code

x = 6, 7, or 8

A = Assembly Location

Y = Year WW = Work Week ■ Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Collector - Emitter Breakdown Voltage		V _{(BR)CEO}				V
$(I_C = -2.0 \text{ mAdc}, I_B = 0)$	BC556	· (BIV)OLO	-65	_	_	-
(.6 =	BC557		-45	_	_	
	BC558		-30	_	_	
Collector - Base Breakdown Voltage		V _{(BR)CBO}				V
$(I_C = -100 \mu\text{Adc})$	BC556	* (BR)CBO	-80	_	_	•
(iC = 100 (a 100)	BC557		-50	_	_	
	BC558		-30	_	_	
Fusition Door Dural down Valtage	20000		-			\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \
Emitter – Base Breakdown Voltage	DOCCO	$V_{(BR)EBO}$	5.0			V
$(I_E = -100 \mu Adc, I_C = 0)$	BC556		-5.0	_	_	
	BC557		-5.0	_	_	
	BC558		-5.0	_	_	
Collector–Emitter Leakage Current		I _{CES}				
$(V_{CES} = -40 \text{ V})$	BC556		_	-2.0	-100	nA
$(V_{CES} = -20 \text{ V})$	BC557		_	-2.0	-100	
	BC558		_	-2.0	-100	
$(V_{CES} = -20 \text{ V}, T_A = 125^{\circ}\text{C})$	BC556		_	_	-4.0	μΑ
	BC557		_	_	-4.0	
	BC558		_	_	-4.0	
ON CHARACTERISTICS			1	ı	I	1
DC Current Gain		h				
	A Sorios Dovice	h _{FE}		90		_
$(I_C = -10 \mu Adc, V_{CE} = -5.0 V)$	A Series Device B Series Devices		_		_	
			_	150 270	_	
$(I_C = -2.0 \text{ mAdc}, V_{CE} = -5.0 \text{ V})$	C Series Devices BC557					
(IC = -2.0 IIIAuc, VCE = -3.0 V)	A Series Device		120 120	170	800 220	
	B Series Devices		180	170 290	460	
	C Series Devices		420	500		
(I 100 mAdo V 50 V)			420	120	800	
$(I_C = -100 \text{ mAdc}, V_{CE} = -5.0 \text{ V})$	A Series Device B Series Devices		_	180	_	
	C Series Devices		_	300	_	
Oallantan Faritan Oatsani'a a Waltana	C Genes Devices		_	300		.,
Collector – Emitter Saturation Voltage		V _{CE(sat)}		0.075	0.0	V
$(I_C = -10 \text{ mAdc}, I_B = -0.5 \text{ mAdc})$			_	-0.075	-0.3	
$(I_C = -10 \text{ mAdc}, I_B = \text{see Note 1})$			_	-0.3	-0.6	
$(I_C = -100 \text{ mAdc}, I_B = -5.0 \text{ mAdc})$			_	-0.25	-0.65	
Base – Emitter Saturation Voltage		$V_{BE(sat)}$				V
$(I_C = -10 \text{ mAdc}, I_B = -0.5 \text{ mAdc})$			_	-0.7	_	
$(I_C = -100 \text{ mAdc}, I_B = -5.0 \text{ mAdc})$			_	-1.0	_	
Base-Emitter On Voltage		V _{BE(on)}				V
$(I_C = -2.0 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc})$		DE(OII)	-0.55	-0.62	-0.7	
$(I_C = -10 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc})$			_	-0.7	-0.82	
SMALL-SIGNAL CHARACTERISTICS					l	1
			1		1	
Current – Gain – Bandwidth Product		f _T				MHz
$(I_C = -10 \text{ mA}, V_{CE} = -5.0 \text{ V}, f = 100 \text{ MHz})$	BC556		_	280	_	
	BC557		_	320	_	
	BC558		_	360	-	
Output Capacitance		C_{ob}	_	3.0	6.0	pF
$(V_{CB} = -10 \text{ V}, I_C = 0, f = 1.0 \text{ MHz})$						
Noise Figure		NF				dB
$(I_C = -0.2 \text{ mAdc}, V_{CE} = -5.0 \text{ V},$	BC556		_	2.0	10	
$R_S = 2.0 \text{ k}\Omega$, $f = 1.0 \text{ kHz}$, $\Delta f = 200 \text{ Hz}$)	BC557		_	2.0	10	
<i>, , , , , , , , , , , , , , , , , , , </i>	BC558		_	2.0	10	
Small-Signal Current Gain		h.		-	-	
	DOSET	h _{fe}	105		000	_
$(I_C = -2.0 \text{ mAdc}, V_{CE} = 5.0 \text{ V}, f = 1.0 \text{ kHz})$	BC557		125	_	900	
	A Series Device B Series Devices		125	_	260	
	D DELIES DEVICES		240	_	500	1
	C Series Devices		450		900	

^{1.} $I_C = -10$ mAdc on the constant base current characteristics, which yields the point $I_C = -11$ mAdc, $V_{CE} = -1.0$ V.

BC557/BC558

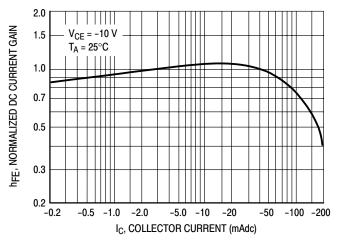


Figure 1. Normalized DC Current Gain

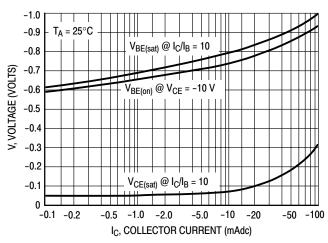


Figure 2. "Saturation" and "On" Voltages

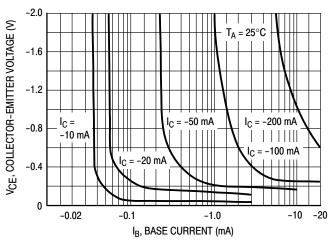


Figure 3. Collector Saturation Region

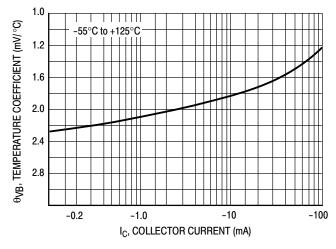


Figure 4. Base-Emitter Temperature Coefficient

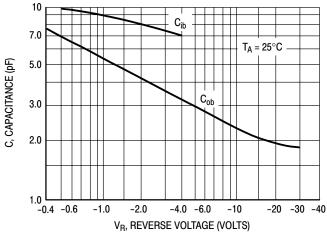


Figure 5. Capacitances

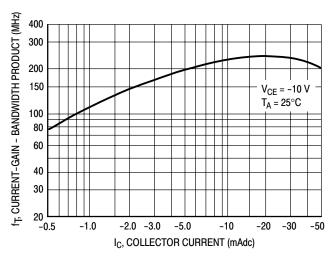


Figure 6. Current-Gain - Bandwidth Product

BC556

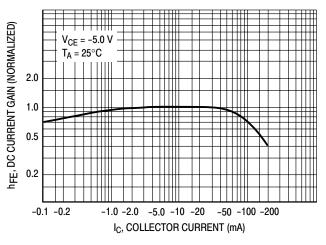


Figure 7. DC Current Gain

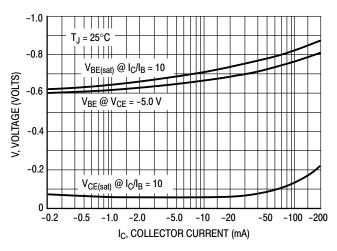


Figure 8. "On" Voltage

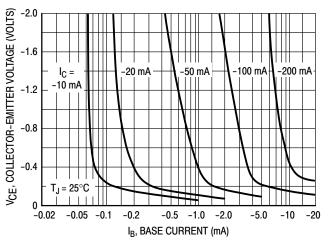


Figure 9. Collector Saturation Region

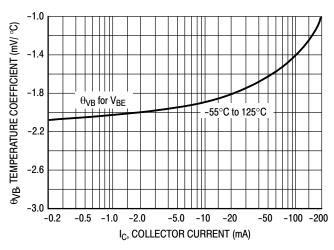


Figure 10. Base-Emitter Temperature Coefficient

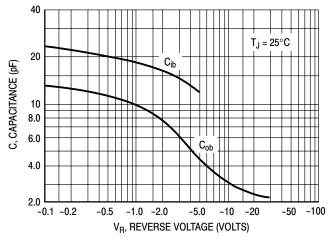


Figure 11. Capacitance

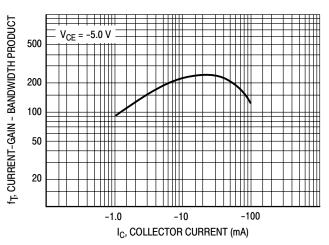


Figure 12. Current-Gain - Bandwidth Product

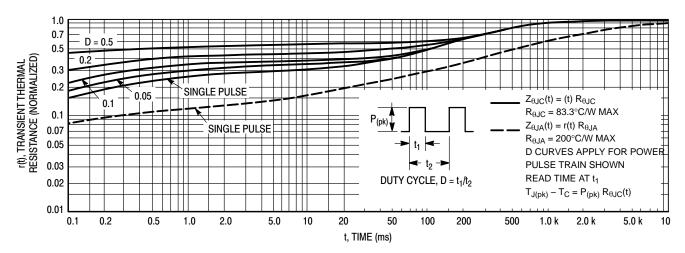


Figure 13. Thermal Response

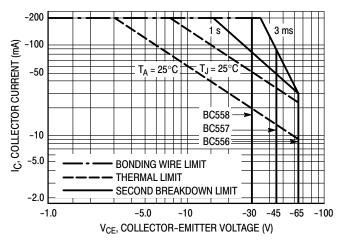


Figure 14. Active Region - Safe Operating Area

The safe operating area curves indicate I_C-V_{CE} limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 14 is based upon $T_{J(pk)} = 150^{\circ}C$; T_{C} or T_{A} is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 13. At high case or ambient temperatures, thermal limitations will reduce the power than can be handled to values less than the limitations imposed by second breakdown.

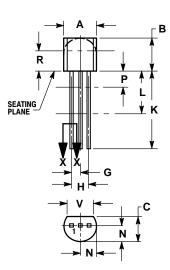
DEVICE ORDERING INFORMATION

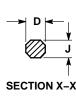
Device	Package	Shipping [†]
BC556B	TO-92	5000 Units / Bulk
BC556BG	TO-92 (Pb-Free)	5000 Units / Bulk
BC556BZL1	TO-92	2000 / Ammo Box
BC556BZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC557AZL1	TO-92	2000 / Ammo Box
BC557AZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC557B	TO-92	5000 Units / Bulk
BC557BG	TO-92 (Pb-Free)	5000 Units / Bulk
BC557BRL1	TO-92	2000 / Tape & Reel
BC557BRL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
BC557BZL1	TO-92	2000 / Ammo Box
BC557BZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC557C	TO-92	5000 Units / Bulk
BC557CG	TO-92 (Pb-Free)	5000 Units / Bulk
BC557CZL1	TO-92	2000 / Ammo Box
BC557CZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC558BRL	TO-92	2000 / Tape & Reel
BC558BRLG	TO-92 (Pb-Free)	2000 / Tape & Reel
BC558BRL1	TO-92	2000 / Tape & Reel
BC558BRL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
BC558BZL1	TO-92	2000 / Ammo Box
BC558BZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC558CZL1	TO-92	2000 / Ammo Box
BC558CZL1G	TO-92 (Pb-Free)	2000 / Ammo Box

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AL**





- DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INC	INCHES		IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
v	0.125		2 //2	

STYLE 17:

PIN 1. COLLECTOR BASE EMITTER

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